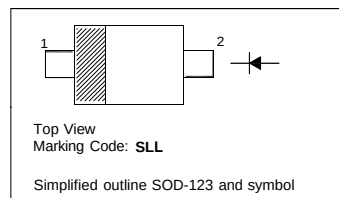


### 0.8A Surface Mount Schottky Barrier Diode

PINNING

| PIN | DESCRIPTION |
|-----|-------------|
| 1   | Cathode     |
| 2   | Anode       |



#### Absolute Maximum Ratings ( $T_a = 25^\circ\text{C}$ )

| Parameter                                                                   | Symbol      | Value         | Unit             |
|-----------------------------------------------------------------------------|-------------|---------------|------------------|
| Reverse Voltage                                                             | $V_R$       | 40            | V                |
| Average Forward Rectified Current                                           | $I_{F(AV)}$ | 0.8           | A                |
| Non-Repetitive Peak Forward Surge Current<br>(8.3 ms Single Half Sine-Wave) | $I_{FSM}$   | 6             | A                |
| Power Dissipation                                                           | $P_{tot}$   | 450           | mW               |
| Operating Temperature Range                                                 | $T_j$       | - 55 to + 125 | $^\circ\text{C}$ |
| Storage Temperature Range                                                   | $T_{stg}$   | - 55 to + 125 | $^\circ\text{C}$ |

#### Characteristics at $T_a = 25^\circ\text{C}$

| Parameter                                                                                   | Symbol      | Min.        | Max.               | Unit |
|---------------------------------------------------------------------------------------------|-------------|-------------|--------------------|------|
| Reverse Breakdown Voltage<br>at $I_R = 1\text{ mA}$                                         | $V_{(BR)R}$ | 40          | -                  | V    |
| Reverse Current<br>at $V_R = 40\text{ V}$<br>at $V_R = 4\text{ V}$<br>at $V_R = 6\text{ V}$ | $I_R$       | -<br>-<br>- | 1<br>0.05<br>0.075 | mA   |
| Forward Voltage<br>at $I_F = 0.1\text{ A}$<br>at $I_F = 0.8\text{ A}$                       | $V_F$       | -<br>-      | 0.45<br>0.62       | V    |
| Total Capacitance<br>at $V_R = 4\text{ V}$ , $f = 1\text{ MHz}$                             | $C_{tot}$   | -           | 120                | pF   |

### Typical Characteristics

1N5819WL

